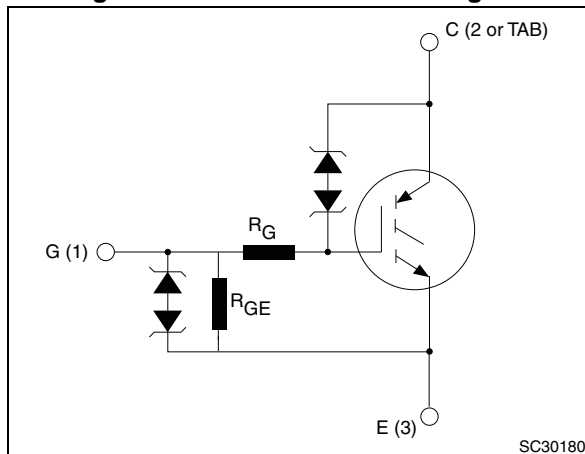


Figure 1. Internal schematic diagram



Features

- Designed for automotive applications and AEC-Q101 qualified
- Low threshold voltage
- Low on-voltage drop
- High voltage clamping feature
- Logic level gate charge
- ESD gate-emitter protection
- Gate and gate-emitter integrated resistors

Application

- Automotive ignition

Description

This application specific IGBT utilizes the most advanced PowerMESH™ technology. The built-in Zener diodes between gate-collector and gate-emitter provide overvoltage protection capabilities. The device also exhibits low on-state voltage drop and low threshold drive for use in automotive ignition system.

Table 1. Device summary

Order codes	Marking	Package	Packaging
STGB35N35LZ-1	GB35N35LZ	I ² PAK	Tube
STGB35N35LZT4	GB35N35LZ	D ² PAK	Tape and reel
STGP35N35LZ	GP35N35LZ	TO-220	Tube

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1 Electrical ratings

Table 2. Absolute maximum ratings

Symbol	Parameter	Value	Unit
V_{CES}	Collector-emitter voltage ($V_{GE} = 0$)	V_{CES} (clamped)	V
V_{ECS}	Emitter collector voltage ($V_{GE} = 0$)	20	V
$I_C^{(1)}$	Continuous collector current at $T_C = 25\text{ °C}$	40	A
$I_C^{(1)}$	Continuous collector current at $T_C = 100\text{ °C}$	30	A
$I_{CP}^{(2)}$	Pulsed collector current	80	A
V_{GE}	Gate-emitter voltage	V_{GE} (clamped)	V
P_{TOT}	Total dissipation at $T_C = 25\text{ °C}$	176	W
E_{AS}	Single pulse energy ($T_C=25\text{ °C}$, $L=1.6\text{ mH}$, $I_C = 22\text{ A}$, $V_{CC} = 50\text{ V}$)	450	mJ
ESD	Human body model ($R=1,5\text{ k}\Omega$, $C=100\text{ pF}$)	8	kV
	Machine model ($R=0$, $C=100\text{ pF}$)	800	V
	Charged device model	2	kV
T_{stg}	Storage temperature	- 55 to 175	°C
T_j	Operating junction temperature		

1. Calculated according to the iterative formula:

$$I_C(T_C) = \frac{T_{j(max)} - T_C}{R_{thj-c} \times V_{CE(sat)(max)}(T_{j(max)}, I_C(T_C))}$$

2. Pulse width limited by maximum junction temperature

Table 3. Thermal data

Symbol	Parameter	Value	Unit
$R_{thj-case}$	Thermal resistance junction-case	0.85	°C/W
$R_{thj-amb}$	Thermal resistance junction-ambient	62.5	°C/W

2 Electrical characteristics

($T_j = 25\text{ °C}$ unless otherwise specified)

Table 4. Static

Symbol	Parameter	Test conditions	Min.	Typ.	Max.	Unit
$V_{CES(\text{clamped})}$	Collector emitter clamped voltage ($V_{GE}=0$)	$I_C=2\text{ mA}$,		345		V
		$I_C=2\text{ mA}$, $T_j = -40\text{ °C to }150\text{ °C}$	320		380	V
$V_{(BR)ECS}$	Emitter collector break-down voltage ($V_{GE}=0$)	$I_C = 75\text{ mA}$	20	28		V
$V_{GE(\text{clamped})}$	Gate emitter clamped voltage	$I_G = \pm 2\text{ mA}$	12	14	16	V
I_{CES}	Collector cut-off current ($V_{GE} = 0$)	$V_{CE} = 15\text{ V}$, $T_j = 150\text{ °C}$			10	μA
		$V_{CE} = 200\text{ V}$, $T_j = 150\text{ °C}$			100	μA
I_{GES}	Gate-emitter leakage current ($V_{CE} = 0$)	$V_{GE} = \pm 10\text{ V}$	500	625	830	μA
R_{GE}	Gate emitter resistance		12	15	20	$\text{k}\Omega$
R_G	Gate resistance			1.5		$\text{k}\Omega$
$V_{GE(\text{th})}$	Gate threshold voltage	$V_{CE} = V_{GE}$, $I_C = 1\text{ mA}$, $T_j = -40\text{ °C}$	1.4			V
		$V_{CE} = V_{GE}$, $I_C = 1\text{ mA}$	1.2	1.6	2.3	V
		$V_{CE} = V_{GE}$, $I_C = 1\text{ mA}$, $T_j = 150\text{ °C}$	0.7			V
$V_{CE(\text{sat})}$	Collector-emitter saturation voltage	$V_{GE} = 4.5\text{ V}$, $I_C = 10\text{ A}$		1.15	1.5	V
		$V_{GE} = 4.5\text{ V}$, $I_C = 15\text{ A}$		1.3	1.7	V

Table 5. Dynamic

Symbol	Parameter	Test conditions	Min.	Typ.	Max.	Unit
C_{ies}	Input capacitance	$V_{CE} = 25\text{ V}$, $f = 1\text{ MHz}$, $V_{GE} = 0$	-	700	-	pF
C_{oes}	Output capacitance		-	150	-	pF
C_{res}	Reverse transfer capacitance		-	6	-	pF
Q_g	Gate charge	$V_{CE} = 280\text{ V}$, $I_C = 15\text{ A}$, $V_{GE} = 5\text{ V}$	-	49	-	nC

Table 6. Functional characteristics

Symbol	Parameter	Test conditions	Min.	Typ.	Max.	Unit
U.I.S.	Functional test open secondary coil	$R_G = 0$, $T_j = 150\text{ °C}$, $V_{CC} = 50\text{ V}$, $V_{GE} = 5\text{ V}$, $L = 1.6\text{ mH}$	18	-	-	A

Table 7. Switching time

Symbol	Parameter	Test conditions	Min.	Typ.	Max.	Unit
$t_{d(on)}$ t_r	Resistive load	$V_{CC} = 14\text{ V}$, $R_L = 1\ \Omega$, $V_{GE} = 5\text{ V}$	-	1.1	-	μs
	Turn-on delay time					μs
	Rise time					μs
$t_{d(on)}$ t_r	Resistive load	$V_{CC} = 14\text{ V}$, $R_L = 1\ \Omega$, $V_{GE} = 5\text{ V}$ $T_j = 150\text{ °C}$	-	1	-	μs
	Turn-on delay time					μs
	Rise time					μs
$t_{d(off)}$ t_f dv/dt	Inductive load	$V_{CC} = 300\text{ V}$, $L = 1\text{ mH}$ $I_C = 15\text{ A}$, $V_{GE} = 5\text{ V}$	-	26.5	-	μs
	Turn-off delay time					μs
	Fall time					μs
$t_{d(off)}$ t_f dv/dt	Inductive load	$V_{CC} = 300\text{ V}$, $L = 1\text{ mH}$ $I_C = 15\text{ A}$, $V_{GE} = 5\text{ V}$ $T_j = 150\text{ °C}$	-	28	-	μs
	Turn-off delay time					μs
	Fall time					μs
$t_{d(off)}$ t_f dv/dt	Inductive load	$V_{CC} = 300\text{ V}$, $L = 1\text{ mH}$ $I_C = 15\text{ A}$, $V_{GE} = 5\text{ V}$ $T_j = 150\text{ °C}$	-	9	-	μs
	Turn-off delay time					μs
	Fall time					μs
$t_{d(off)}$ t_f dv/dt	Inductive load	$V_{CC} = 300\text{ V}$, $L = 1\text{ mH}$ $I_C = 15\text{ A}$, $V_{GE} = 5\text{ V}$ $T_j = 150\text{ °C}$	-	65	-	μs
	Turn-off delay time					μs
	Fall time					μs
$t_{d(off)}$ t_f dv/dt	Inductive load	$V_{CC} = 300\text{ V}$, $L = 1\text{ mH}$ $I_C = 15\text{ A}$, $V_{GE} = 5\text{ V}$ $T_j = 150\text{ °C}$	-	65	-	μs
	Turn-off delay time					μs
	Fall time					μs

2.1 Electrical characteristics (curves)

Figure 2. Collector-emitter saturation voltage vs temperature

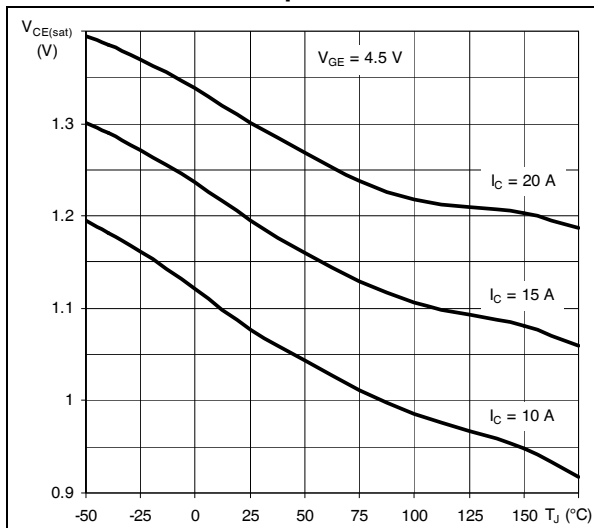


Figure 3. Self clamped inductive switch

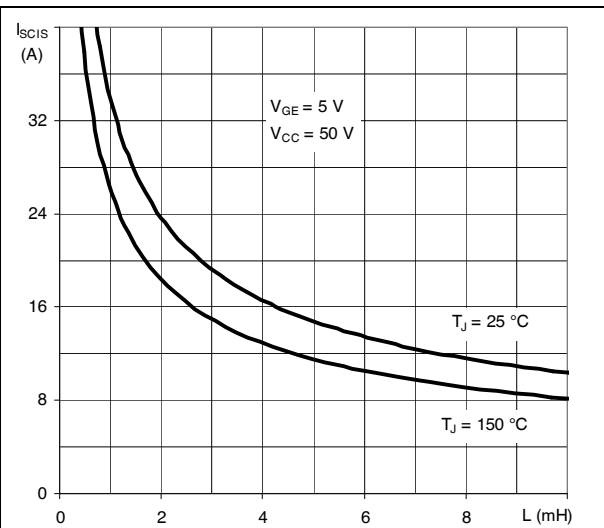


Figure 4. Output characteristics ($T_J = 25^{\circ}C$)

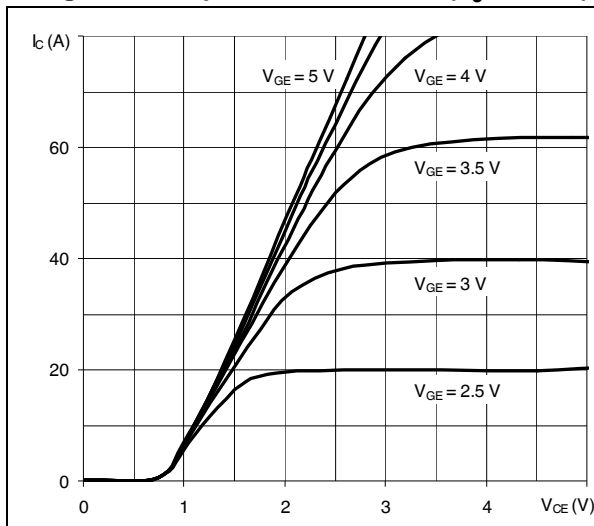


Figure 5. Output characteristics ($T_J = -40^{\circ}C$)

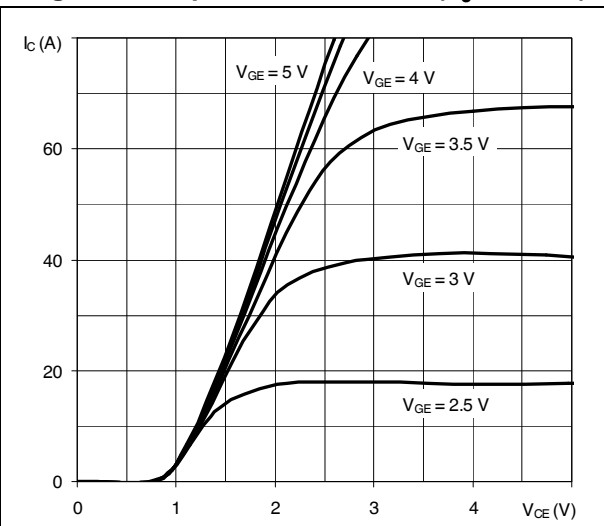


Figure 6. Output characteristics ($T_J = 175\text{ }^\circ\text{C}$)

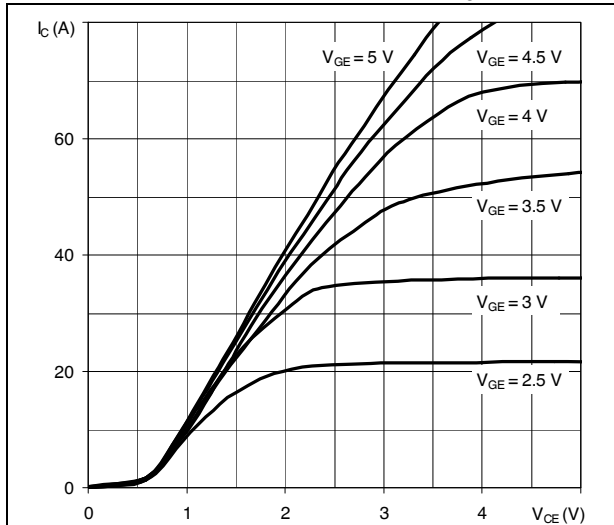


Figure 7. Transfer characteristics

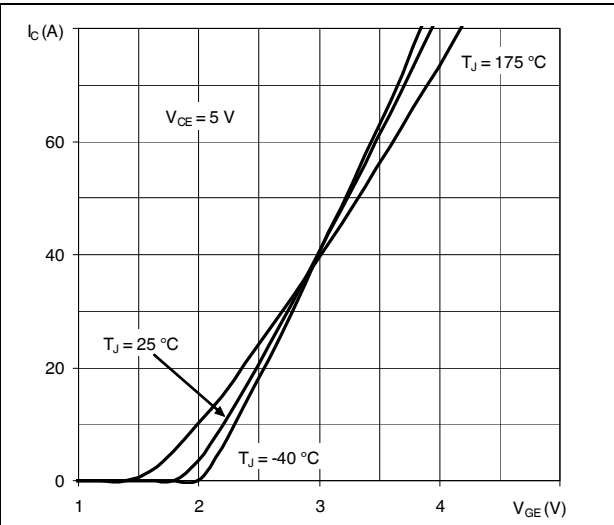


Figure 8. Collector cut-off current vs temperature

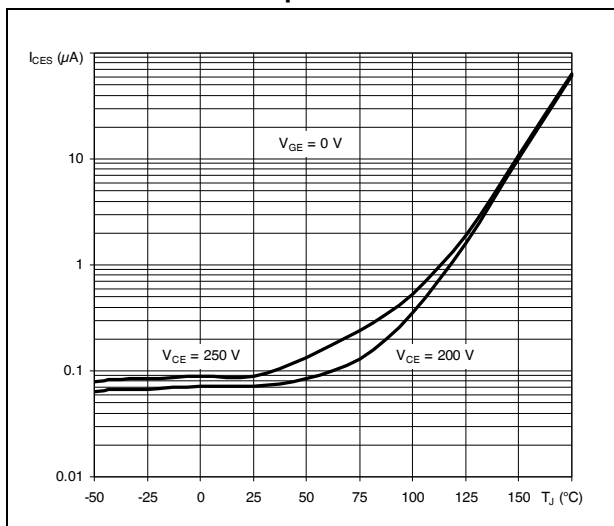


Figure 9. Normalized collector emitter voltage vs temperature

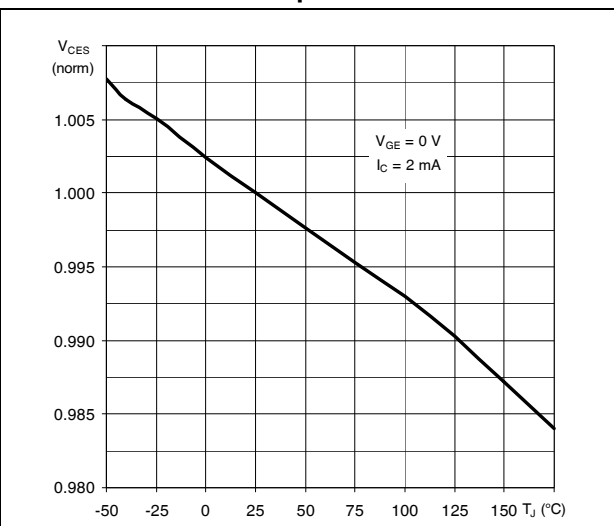


Figure 10. Normalized gate threshold voltage vs temperature

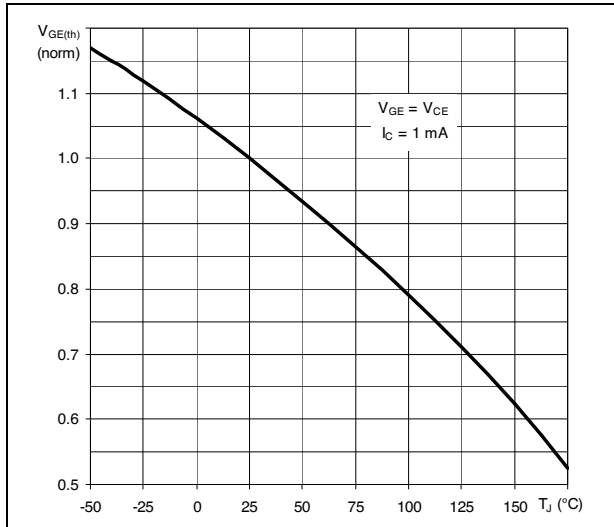


Figure 11. Gate charge

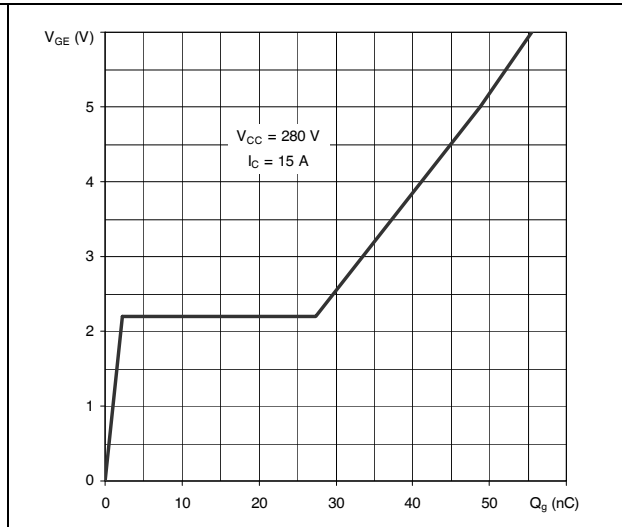
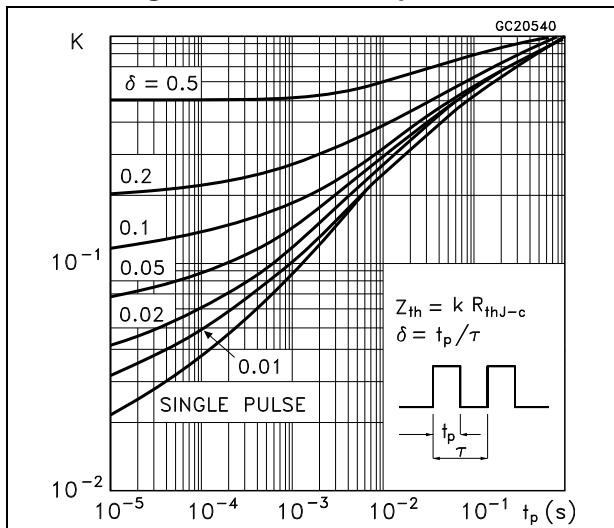


Figure 12. Thermal impedance



3 Test circuits

Figure 13. Test circuit for inductive load switching

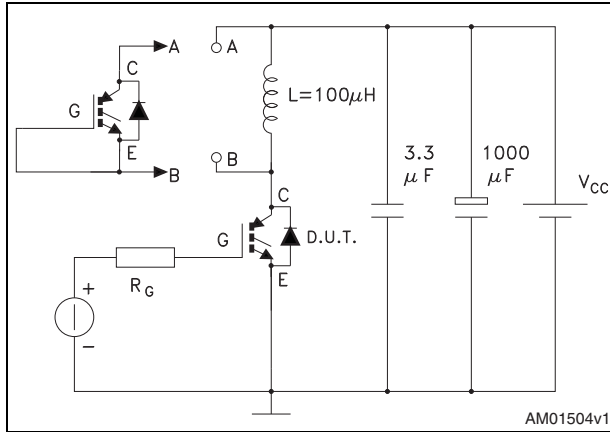


Figure 14. Gate charge test circuit

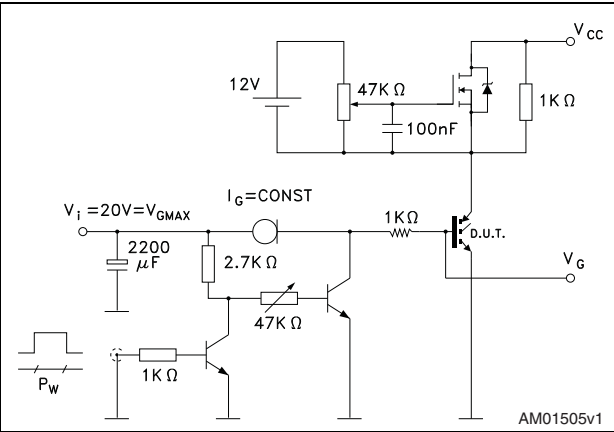
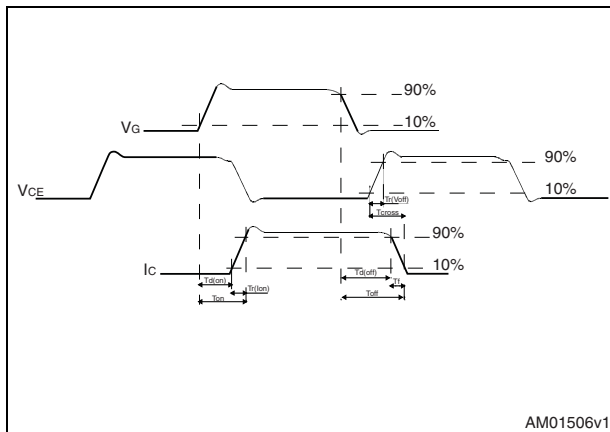


Figure 15. Switching waveform



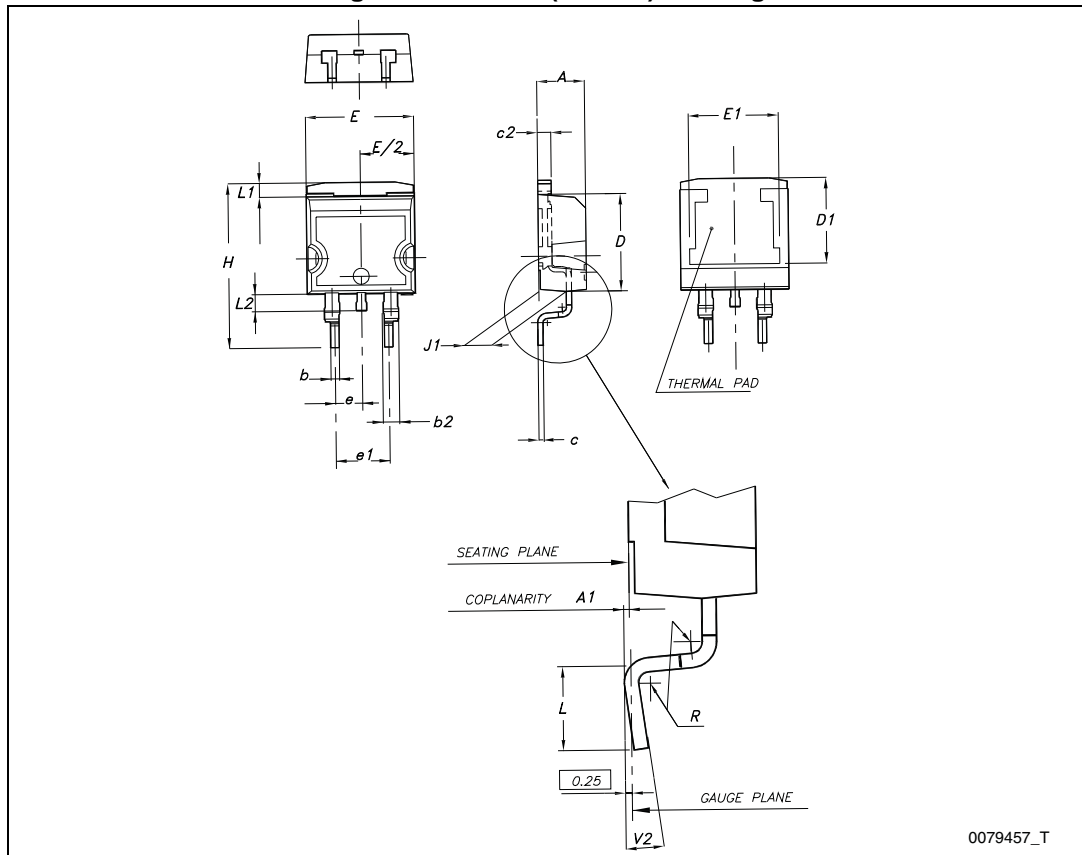
4 Package mechanical data

In order to meet environmental requirements, ST offers these devices in different grades of ECOPACK[®] packages, depending on their level of environmental compliance. ECOPACK[®] specifications, grade definitions and product status are available at: www.st.com. ECOPACK is an ST trademark.

Table 8. D²PAK (TO-263) mechanical data

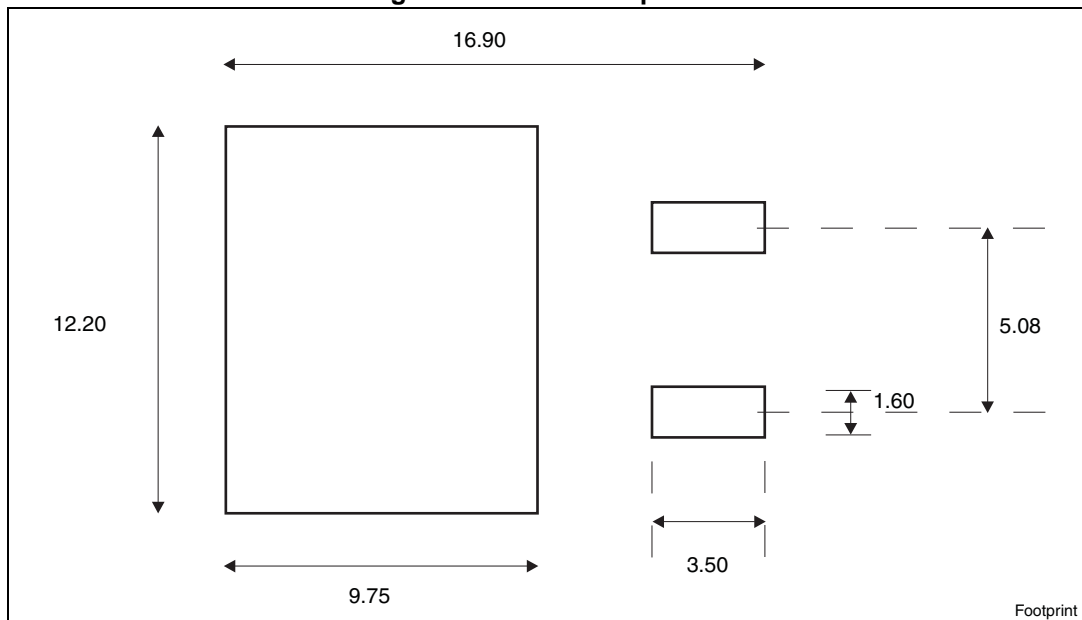
Dim.	mm		
	Min.	Typ.	Max.
A	4.40		4.60
A1	0.03		0.23
b	0.70		0.93
b2	1.14		1.70
c	0.45		0.60
c2	1.23		1.36
D	8.95		9.35
D1	7.50		
E	10		10.40
E1	8.50		
e		2.54	
e1	4.88		5.28
H	15		15.85
J1	2.49		2.69
L	2.29		2.79
L1	1.27		1.40
L2	1.30		1.75
R		0.4	
V2	0°		8°

Figure 16. D²PAK (TO-263) drawing



0079457_T

Figure 17. D²PAK footprint^(a)

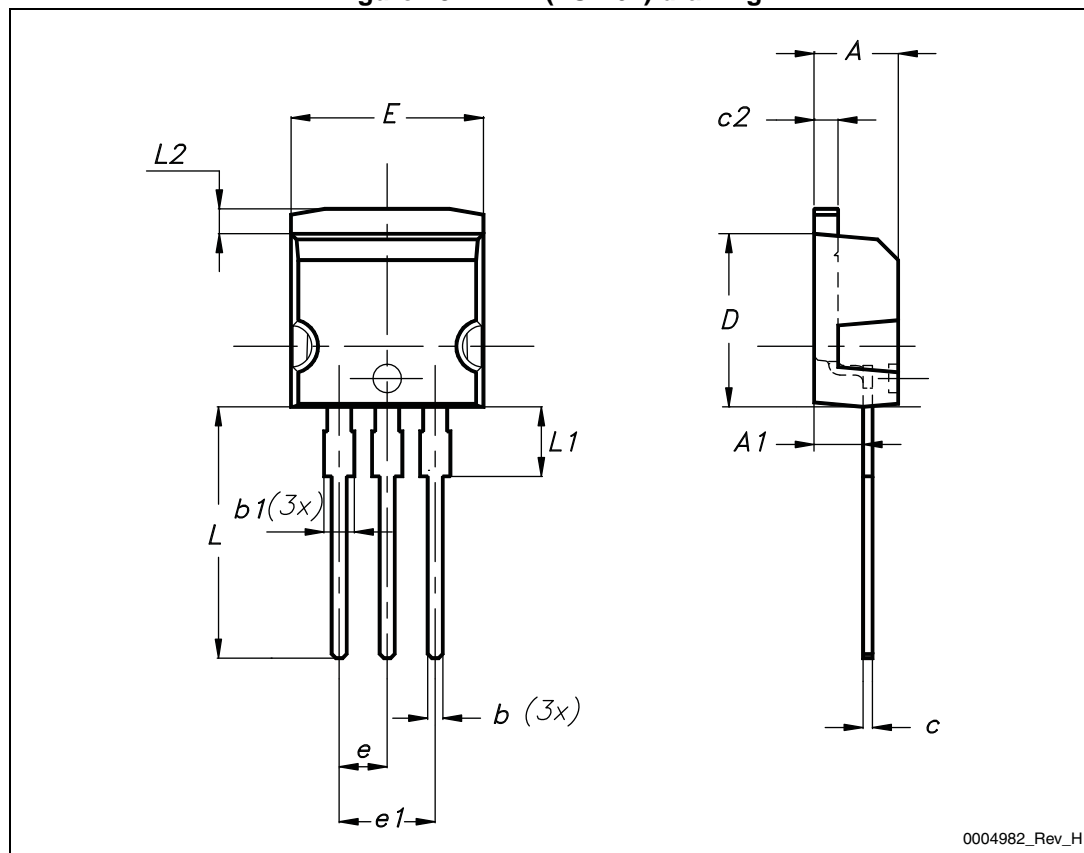


a. All dimension are in millimeters

Table 9. I²PAK (TO-262) mechanical data

DIM.	mm.		
	min.	typ	max.
A	4.40		4.60
A1	2.40		2.72
b	0.61		0.88
b1	1.14		1.70
c	0.49		0.70
c2	1.23		1.32
D	8.95		9.35
e	2.40		2.70
e1	4.95		5.15
E	10		10.40
L	13		14
L1	3.50		3.93
L2	1.27		1.40

Figure 18. I²PAK (TO-262) drawing

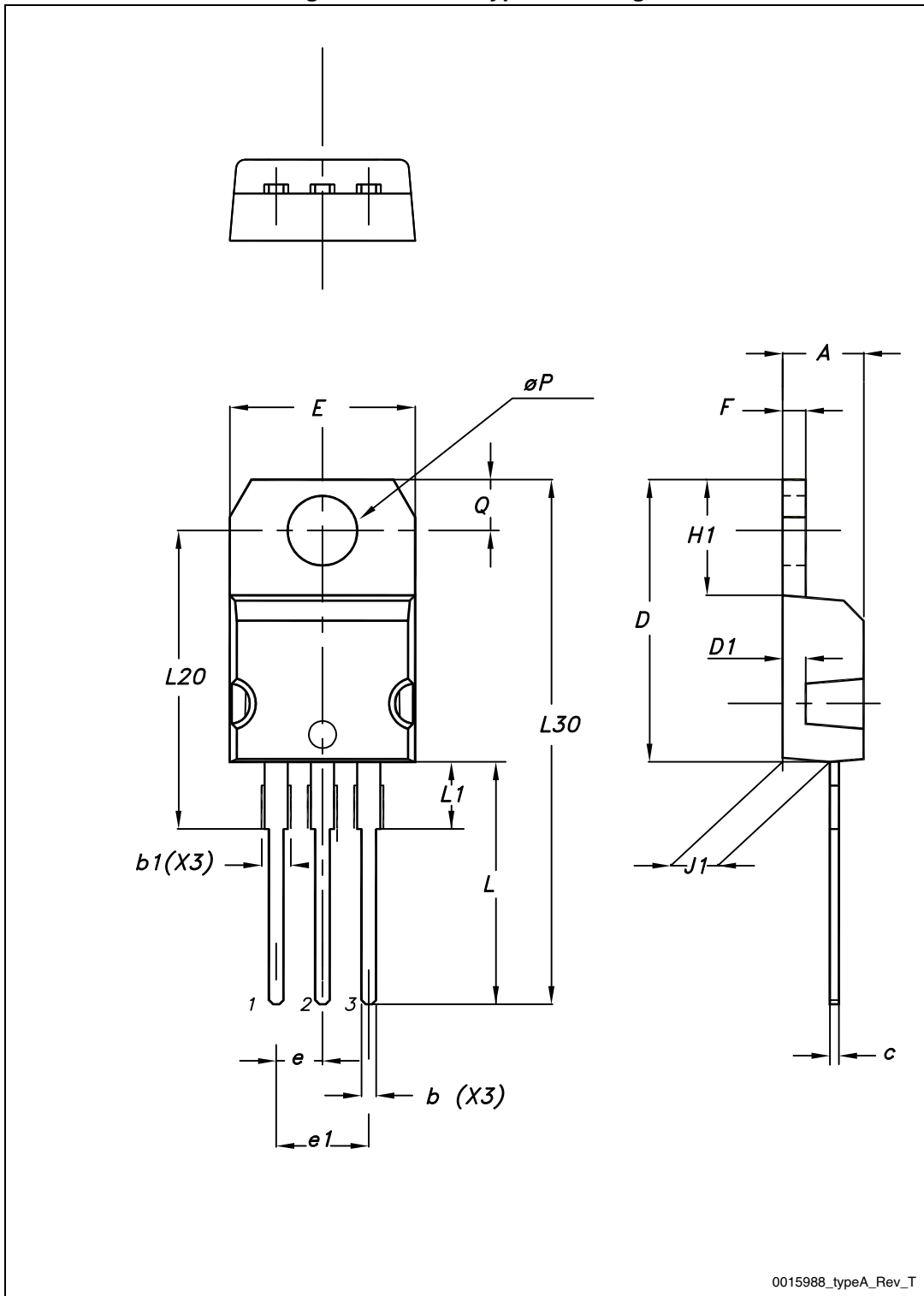


0004982_Rev_H

Table 10. TO-220 type A mechanical data

Dim.	mm		
	Min.	Typ.	Max.
A	4.40		4.60
b	0.61		0.88
b1	1.14		1.70
c	0.48		0.70
D	15.25		15.75
D1		1.27	
E	10		10.40
e	2.40		2.70
e1	4.95		5.15
F	1.23		1.32
H1	6.20		6.60
J1	2.40		2.72
L	13		14
L1	3.50		3.93
L20		16.40	
L30		28.90	
ØP	3.75		3.85
Q	2.65		2.95

Figure 19. TO-220 type A drawing



5 Packaging mechanical data

Table 11. D²PAK (TO-263) tape and reel mechanical data

Tape			Reel		
Dim.	mm		Dim.	mm	
	Min.	Max.		Min.	Max.
A0	10.5	10.7	A		330
B0	15.7	15.9	B	1.5	
D	1.5	1.6	C	12.8	13.2
D1	1.59	1.61	D	20.2	
E	1.65	1.85	G	24.4	26.4
F	11.4	11.6	N	100	
K0	4.8	5.0	T		30.4
P0	3.9	4.1			
P1	11.9	12.1		Base qty	1000
P2	1.9	2.1		Bulk qty	1000
R	50				
T	0.25	0.35			
W	23.7	24.3			

Figure 20. Tape for D²PAK (TO-263)

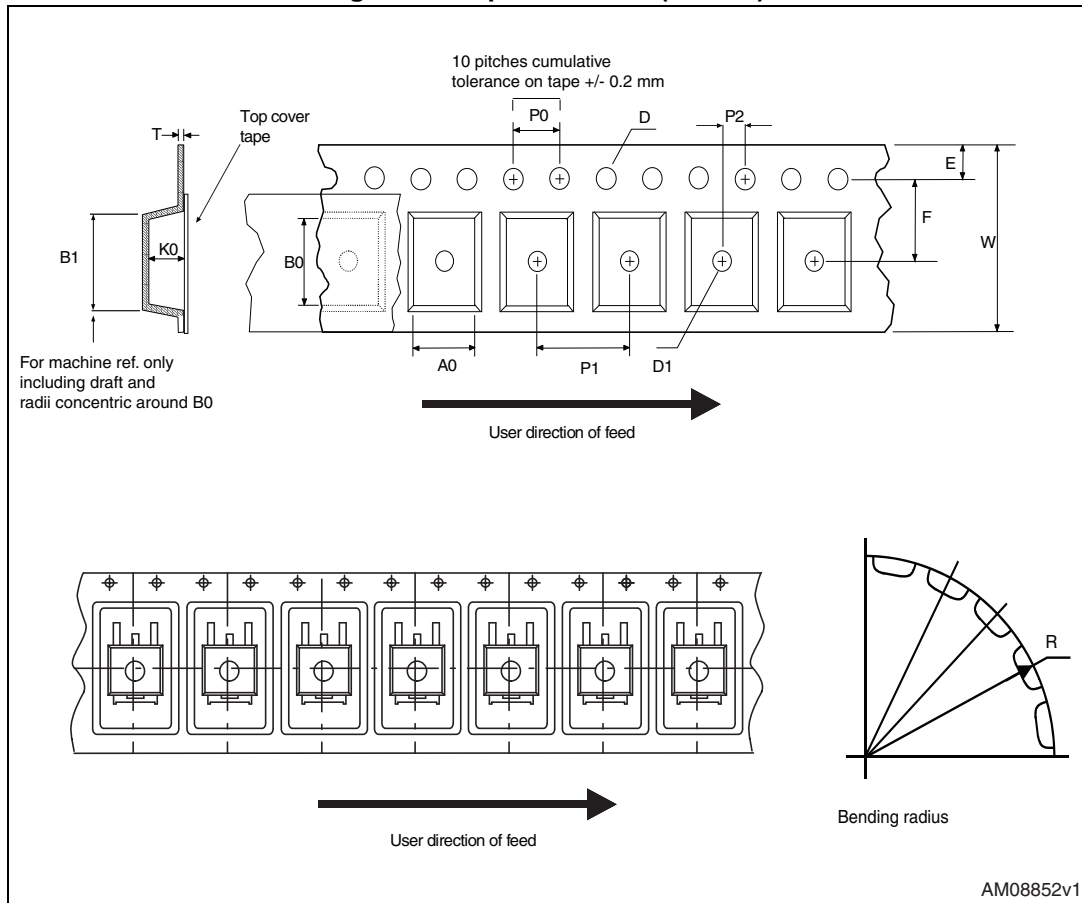
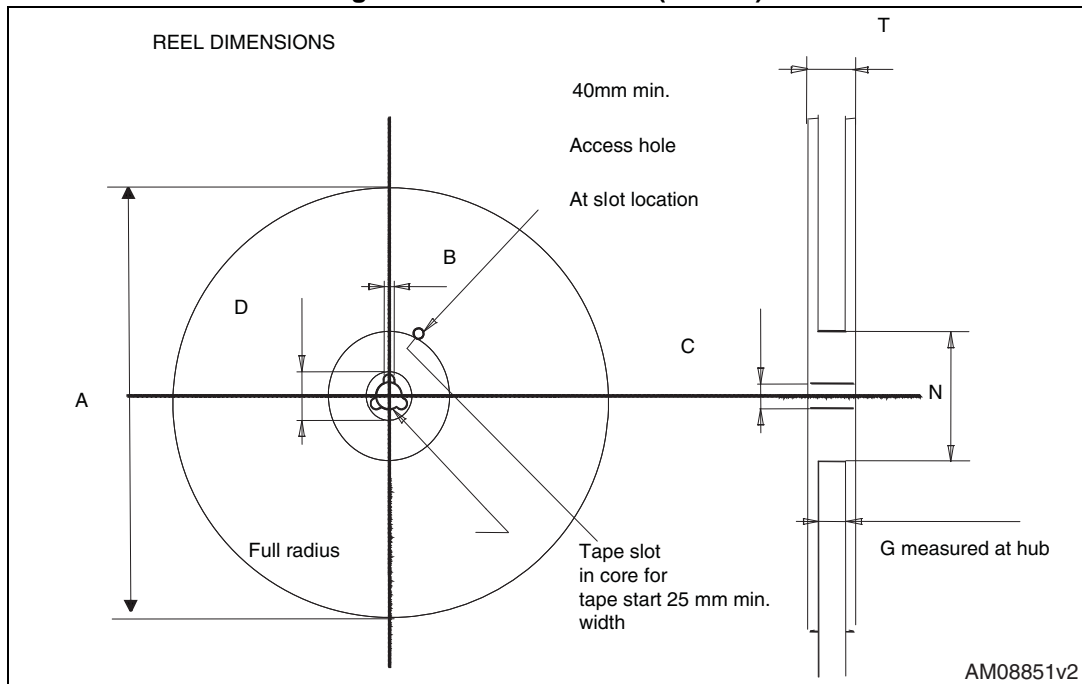


Figure 21. Reel for D²PAK (TO-263)



6 Revision history

Table 12. Document revision history

Date	Revision	Changes
29-Mar-2006	1	Initial release.
03-Jun-2009	2	Document status promoted from preliminary data to datasheet.
05-Nov-2009	3	Inserted Chapter 2.1: Electrical characteristics (curves)
16-Feb-2010	4	Added new package, mechanical data: TO-220
03-Jun-2010	5	<ul style="list-style-type: none">– Added Figure 12: Thermal impedance– Modified Figure 4, Figure 5, Figure 6 and Figure 7– D²PAK mechanical data has been updated
28-May-2013	6	<ul style="list-style-type: none">– Updated title in cover page, Chapter 5: Packaging mechanical data and Chapter 5: Packaging mechanical data.

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